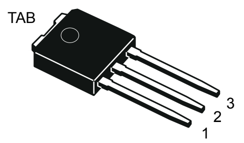
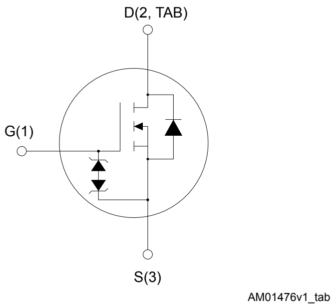
STD3NK80Z-1

Datasheet

N-channel 800 V, 3.6 Ω typ., 2.5 A SuperMESH Power MOSFET in an IPAK package



IPAK



Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D
STD3NK80Z-1	800 V	4.5 Ω	2.5 A

- 100% avalanche tested
- Gate charge minimized
- Very low intrinsic capacitance
- Zener-protected

Applications

- Switching applications

Description

This high-voltage device is a Zener-protected N-channel Power MOSFET developed using the SuperMESH technology by STMicroelectronics, an optimization of the well-established PowerMESH. In addition to a significant reduction in on-resistance, this device is designed to ensure a high level of dv/dt capability for the most demanding applications.

Product status link
STD3NK80Z-1

Product summary	
Order code	STD3NK80Z-1
Marking	D3NK80Z
Package	IPAK
Packing	Tube

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	800	V
V_{GS}	Gate-source voltage	±30	V
I_D	Drain current (continuous) at T_C = 25 °C	2.5	A
	Drain current (continuous) at T_C = 100 °C	1.57	
I_{DM} [(1)]	Drain current (pulsed)	10	A
P_{TOT}	Total power dissipation at T_C = 25 °C	70	W
ESD	Gate-source, human body model (R = 1.5 kΩ, C = 100 pF)	2	kV
dv/dt [(2)]	Peak diode recovery voltage slope	4.5	V/ns
T_{stg}	Storage temperature range	-55 to 150	°C
T_J	Operating junction temperature range		°C

1. *Pulse width limited by safe operating area.*
2. *$I_{SD} \leq 2.5$ A, di/dt ≤ 200 A/µs, V_{DS} (Peak) < $V_{(BR)DSS}$, V_{DD} = 640 V.*

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	1.78	°C/W
R_{thJA}	Thermal resistance, junction-to-ambient	100	°C/W

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width is limited by T_J max.)	2.5	A
E_{AS}	Single pulse avalanche energy (starting T_J = 25 °C, I_D = I_{AR}, V_{DD} = 50 V)	170	mJ

2 Electrical characteristics

T_C = 25 °C unless otherwise specified.

Table 4. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 1 mA	800			V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0 V, V_{DS} = 800 V			1	µA
		V_{GS} = 0 V, V_{DS} = 800 V, T_C = 125 °C[(1)]			50	
I_{GSS}	Gate-body leakage current	V_{DS} = 0 V, V_{GS} = ±20 V			±10	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 50 µA	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on- resistance	V_{GS} = 10 V, I_D = 1.25 A		3.6	4.5	Ω

1. *Specified by design, not tested in production.*

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz	-	485	-	pF
C_{oss}	Output capacitance		-	57	-	pF
C_{rss}	Reverse transfer capacitance		-	11	-	pF
$C_{oss\ eq}$[(1)]	Equivalent output capacitance	V_{GS} = 0 V, V_{DS} = 0 to 640 V	-	22	-	pF
Q_g	Total gate charge	V_{DD} = 640 V, I_D = 2.5 A, V_{GS} = 0 to 10 V (see Figure 14. Test circuit for gate charge behavior)	-	19	-	nC
Q_{gs}	Gate-source charge		-	3.2	-	nC
Q_{gd}	Gate-drain charge		-	10.8	-	nC

1. *$C_{oss\ eq}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80%.*

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 400 V, I_D = 1.25 A, R_G = 4.7 Ω, V_{GS} =10 V (see Figure 13. Test circuit for resistive load switching times and Figure 18. Switching time waveform)	-	17	-	ns
t_r	Rise time		-	27	-	ns
$t_{d(off)}$	Turn-off delay time		-	36	-	ns
t_f	Fall time		-	40	-	ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		2.5	A
I_{SDM} (1)	Source-drain current (pulsed)		-		10	A
V_{SD} (2)	Forward on voltage	I_{SD} = 2.5 A, V_{GS} = 0 V	-		1.6	V
t_{rr}	Reverse recovery time	I_{SD} = 2.5 A, di/dt = 100 A/µs V_{DD} = 50 V (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	384		ns
Q_{rr}	Reverse recovery charge		-	1.6		µC
I_{RRM}	Reverse recovery current		-	8.4		A
t_{rr}	Reverse recovery time	I_{SD} = 2.5 A, di/dt = 100 A/µs, V_{DD} = 50 V , T_J = 150 °C (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	474		ns
Q_{rr}	Reverse recovery charge		-	2.1		µC
I_{RRM}	Reverse recovery current		-	8.8		A

1. *Pulsed: pulse duration = 300 µs, duty cycle 1.5%.*
2. *Pulse width is limited by safe operating area.*

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

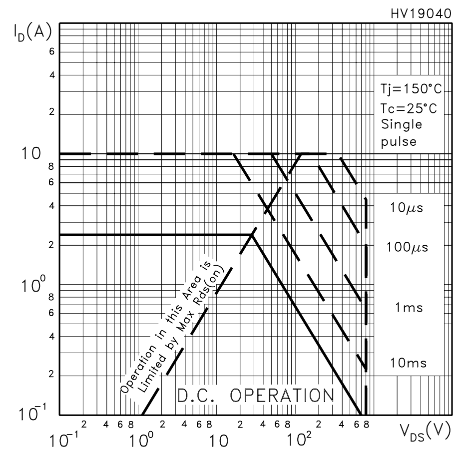


Figure 2. Thermal impedance

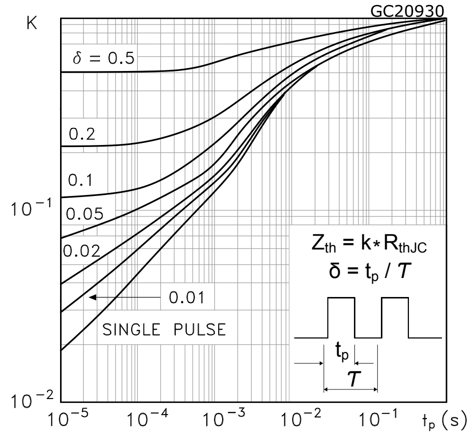


Figure 3. Output characteristics

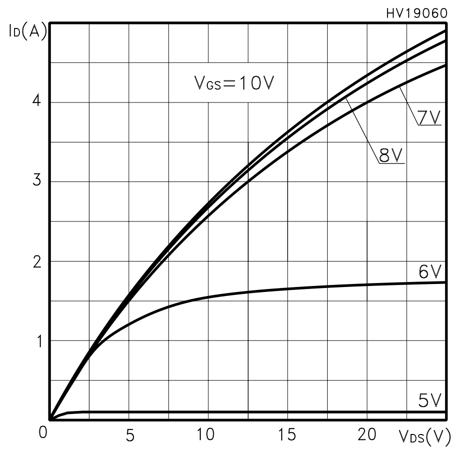


Figure 4. Transfer characteristics

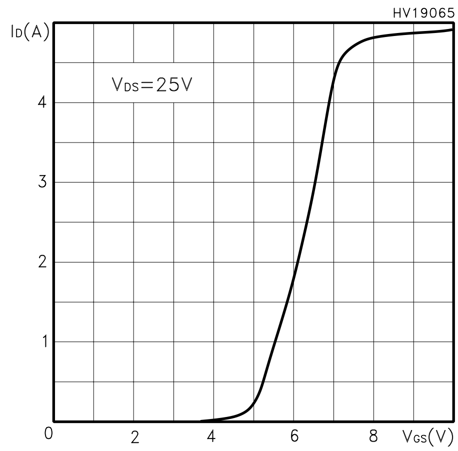


Figure 5. Static drain-source on-resistance

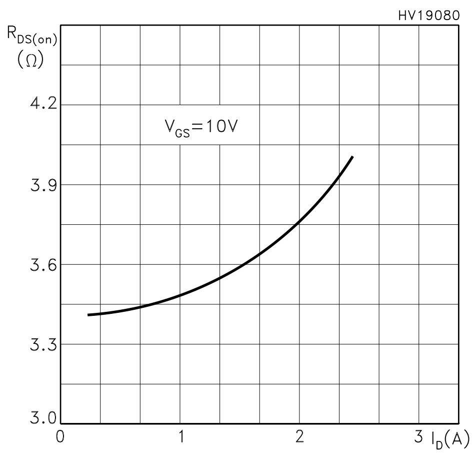


Figure 6. Gate charge vs gate-source voltage

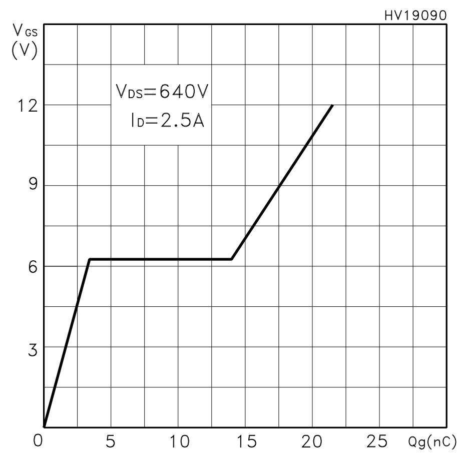


Figure 7. **Capacitance variations**

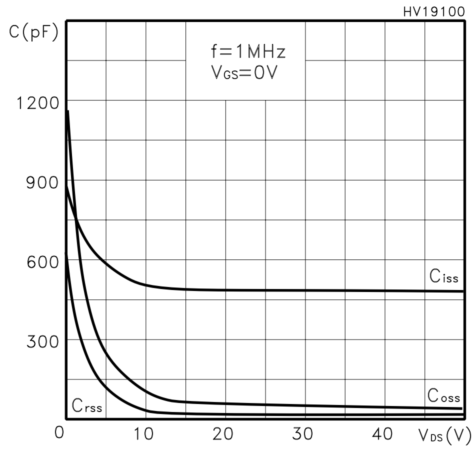


Figure 8. **Normalized gate threshold voltage vs temperature**

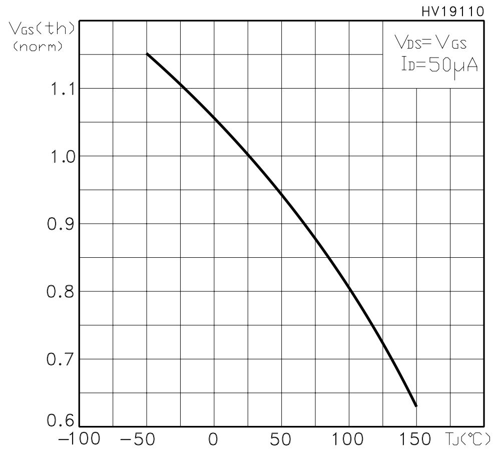


Figure 9. **Normalized on-resistance vs temperature**

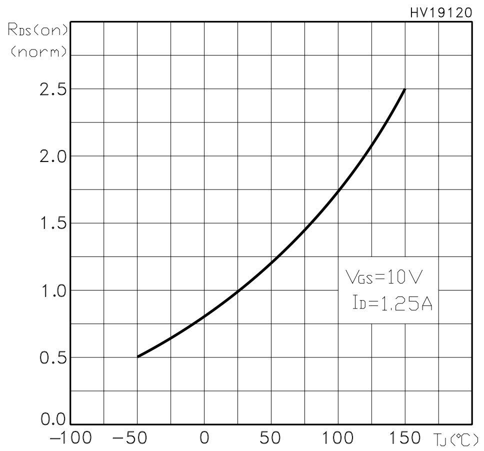


Figure 10. **Source-drain diode forward characteristics**

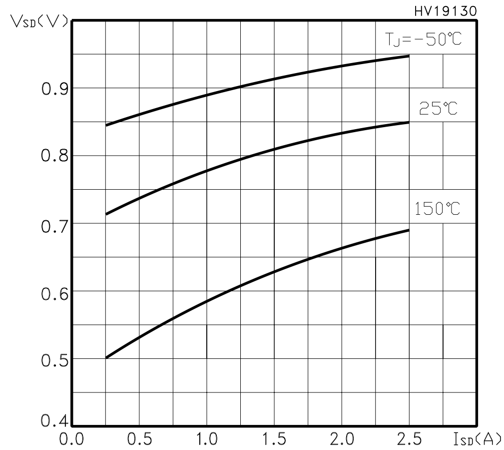


Figure 11. **Normalized $V_{(BR)DSS}$ vs temperature**

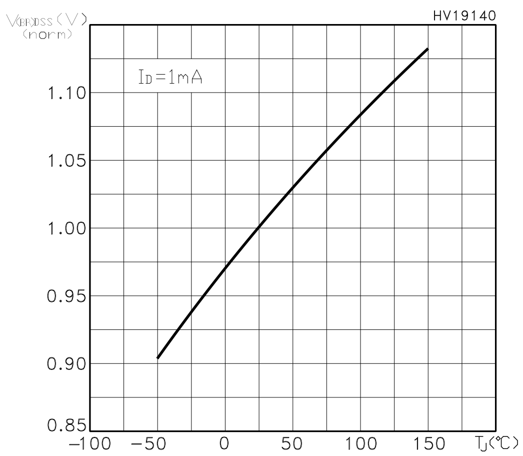
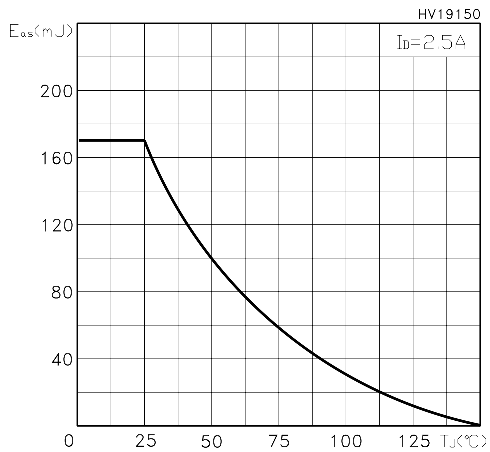


Figure 12. **Maximum avalanche energy vs temperature**



3 Test circuits

Figure 13. Test circuit for resistive load switching times

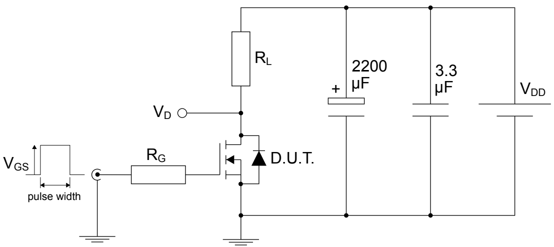


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Figure 14. Test circuit for gate charge behavior

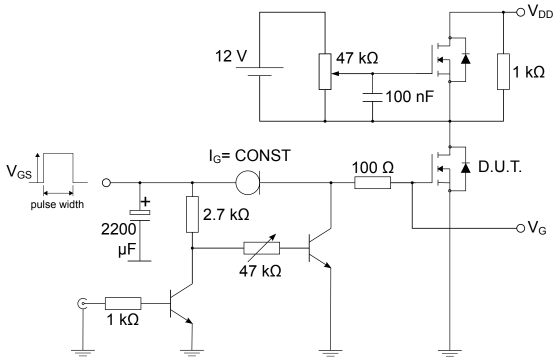

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Figure 15. Test circuit for inductive load switching and diode recovery times

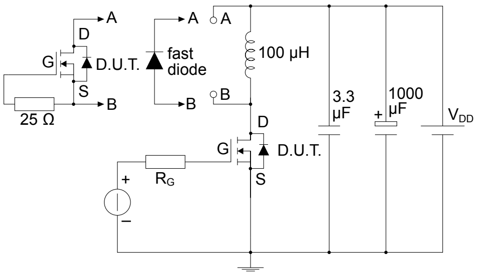

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Figure 16. Unclamped inductive load test circuit

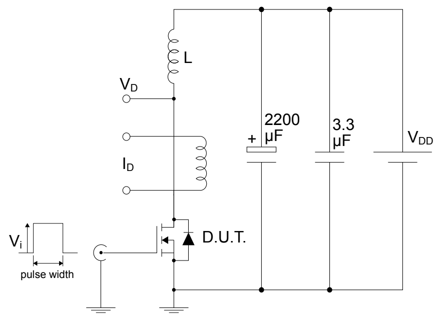

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Figure 17. Unclamped inductive waveform

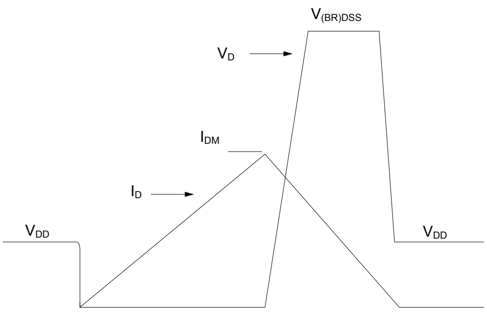

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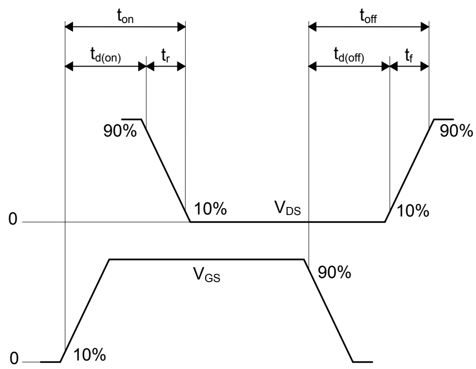
Figure 18. Switching time waveform



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4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 IPAK (TO-251) type C package information

Figure 19. IPAK (TO-251) type C package outline

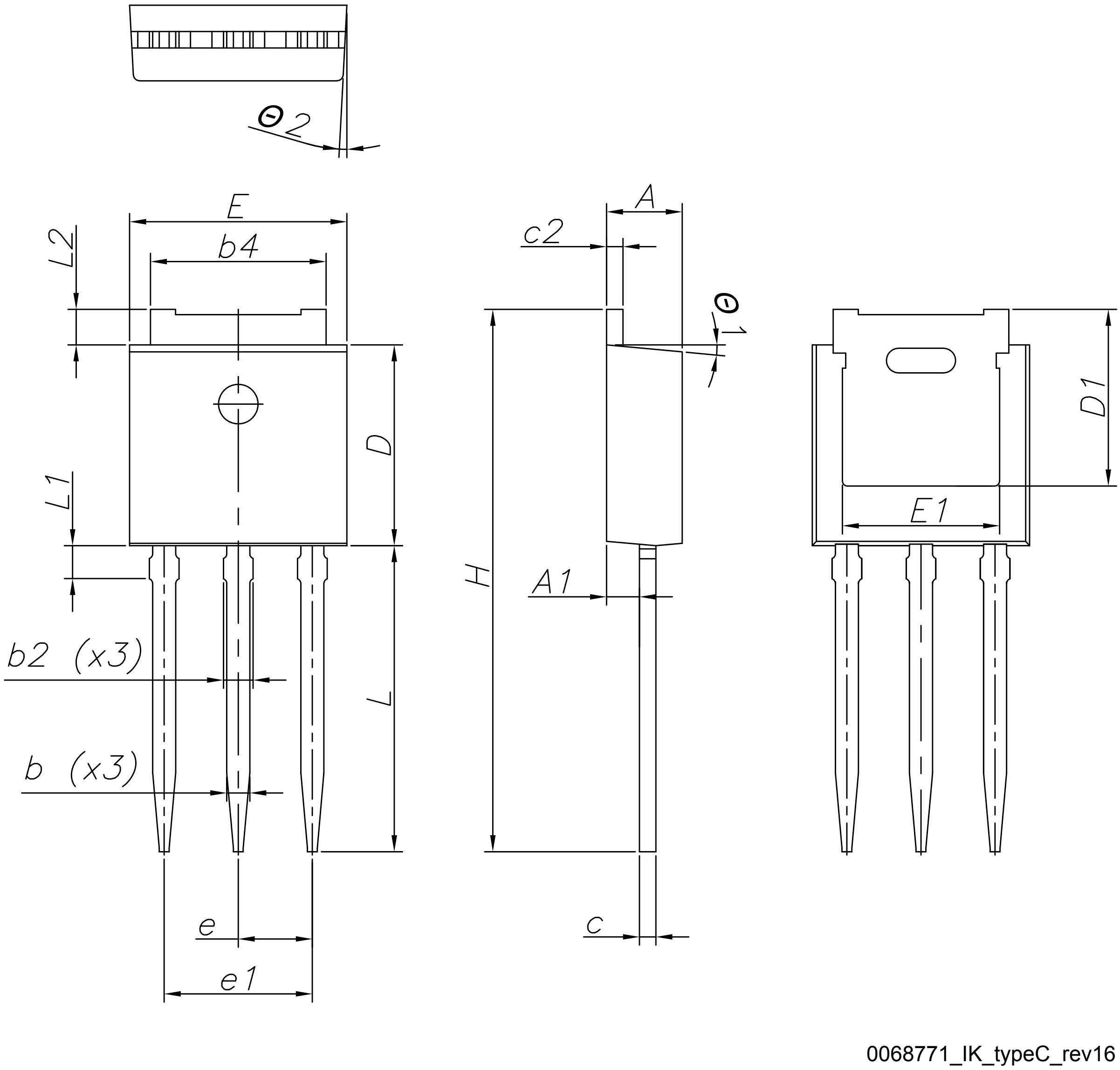

Table 8. IPAK (TO-251) type C package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.35
A1	0.90	1.00	1.10
b	0.66		0.79
b2			0.90
b4	5.23	5.33	5.43
c	0.46		0.59
c2	0.46		0.59
D	6.00	6.10	6.20
D1	5.20	5.37	5.55
E	6.50	6.60	6.70
E1	4.60	4.78	4.95
e	2.20	2.25	2.30
e1	4.40	4.50	4.60
H	16.18	16.48	16.78
L	9.00	9.30	9.60
L1	0.80	1.00	1.20
L2	0.90	1.08	1.25
θ1	3°	5°	7°
θ2	1°	3°	5°

Revision history

Table 9. Document revision history

Date	Revision	Changes
27-Jun-2023	1	First release. The part number STD3NK80Z-1 was previously inserted in the DS3337.

Contents

IMPORTANT NOTICE – READ CAREFULLY